

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	14	((dummy near2 gate) near4 (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	132662	((etch\$4 or strip\$4) near4 (after or subsequent\$4) (grow\$4 or form\$4 or deposit\$4) near4 gate near2 (oxide or dielectric or insulator) (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	17445	((etch\$4 or strip\$4) near4 (after or subsequent\$4) near4 (grow\$4 or form\$4 or deposit\$4) near4 gate near2 (oxide or dielectric or insulator) (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
4	BRS	L4	0	((etch\$4 or strip\$4) near4 (after or subsequent\$4) near4 (grow\$4 or form\$4 or deposit\$4) near4 gate near2 (oxide or dielectric or insulator) near4 (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor)))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	2	((etch\$4 or strip\$4) near8 (after or subsequent\$4) near8 (grow\$4 or form\$4 or deposit\$4) near8 gate near8 (oxide or dielectric or insulator) near8 (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor)))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	21	((etch\$4 or strip\$4) same (after or subsequent\$4) same (grow\$4 or form\$4 or deposit\$4) near16 gate near4 (oxide or dielectric or insulator) near8 (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor)))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
7	BRS	L7	1	((etch\$4 or strip\$4) near8 (open\$4 or hole or space or trench) near8 (grow\$4 or form\$4 or deposit\$4) near4 gate near4 (oxide or dielectric or insulator) near8 (select\$4 near2 ((mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) or transistor))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB